



SEMITRANS™ 3

Trench IGBT Modules

SKM 200GB126D

SKM 200GAL126D

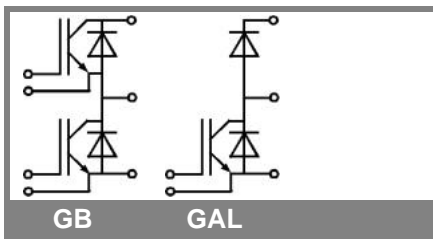
Preliminary Data

Features

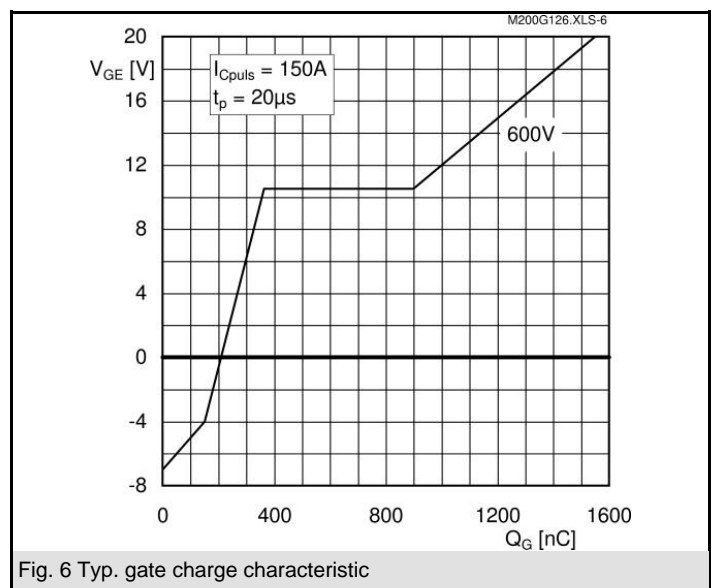
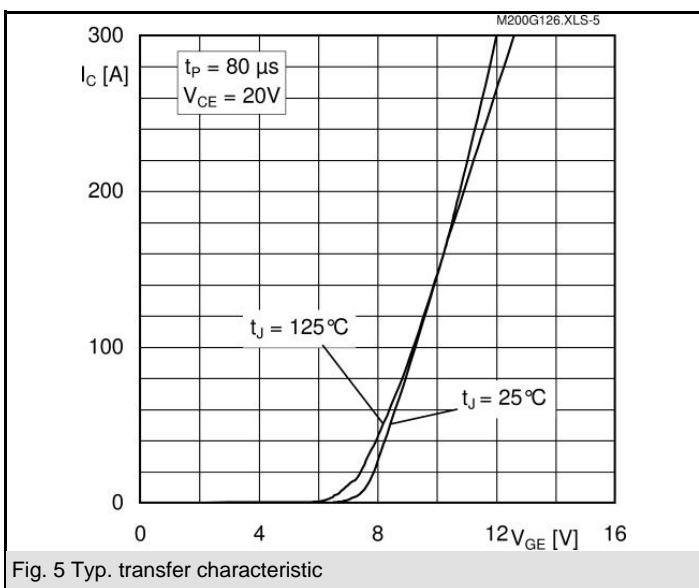
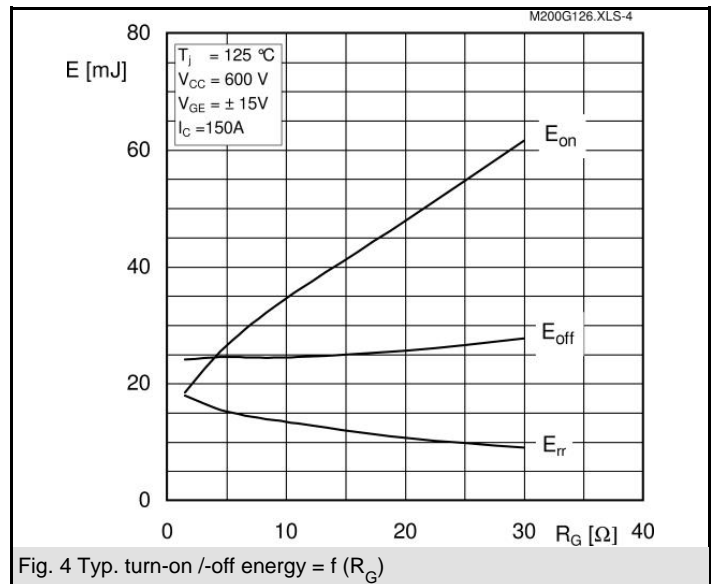
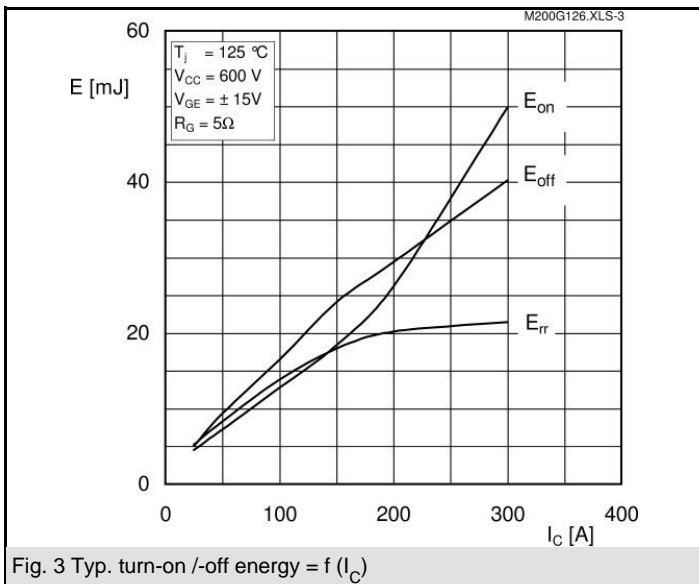
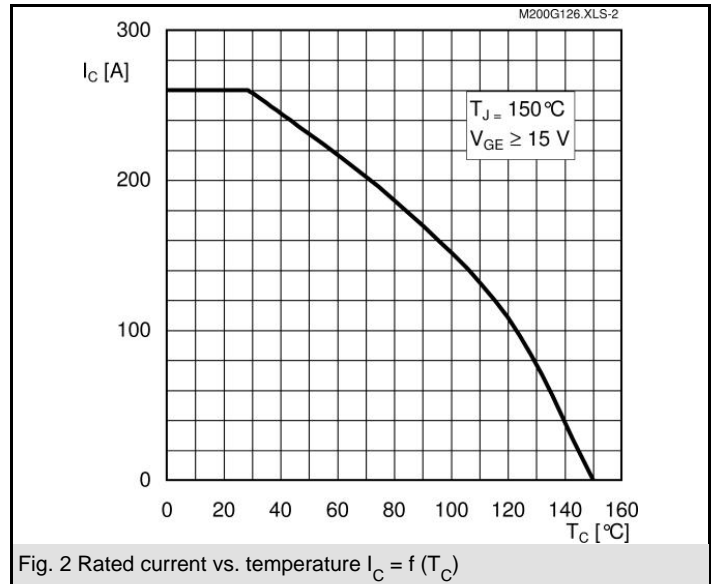
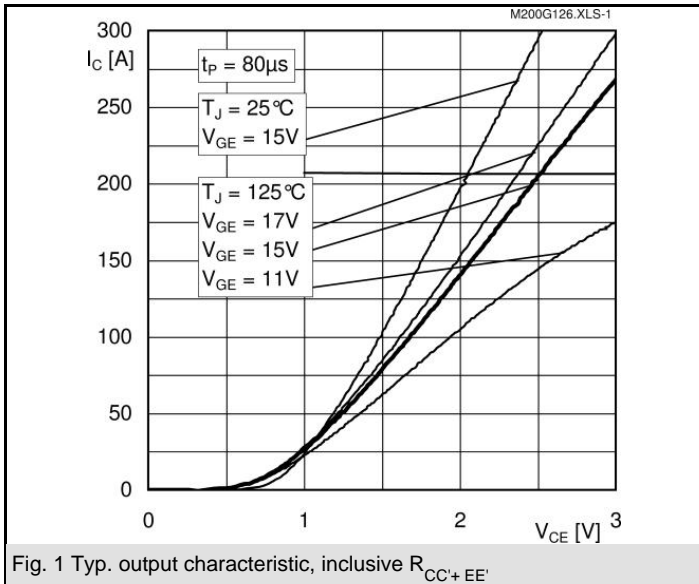
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

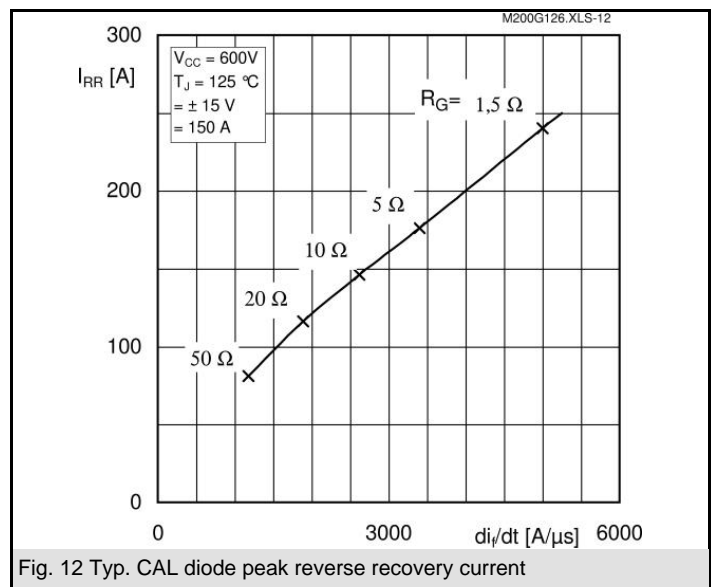
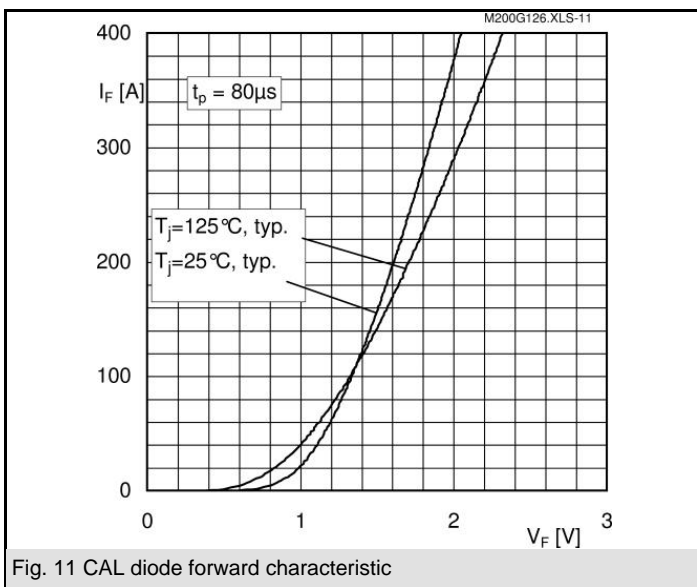
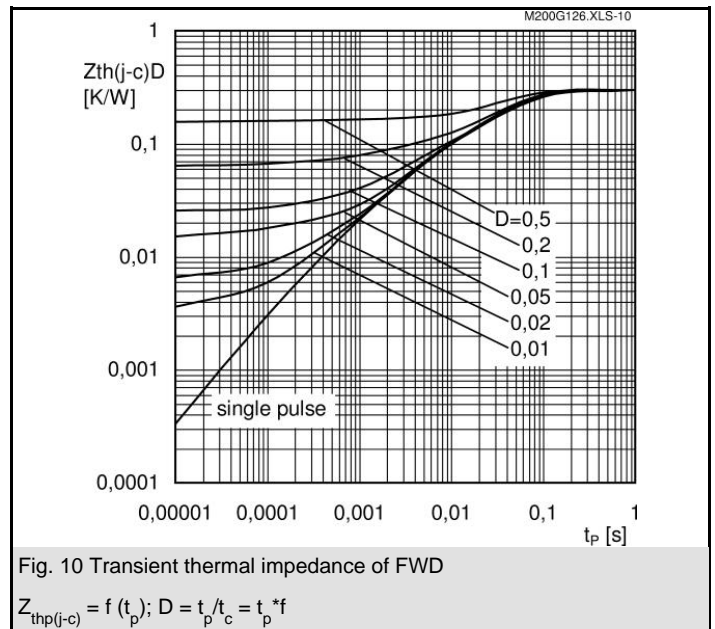
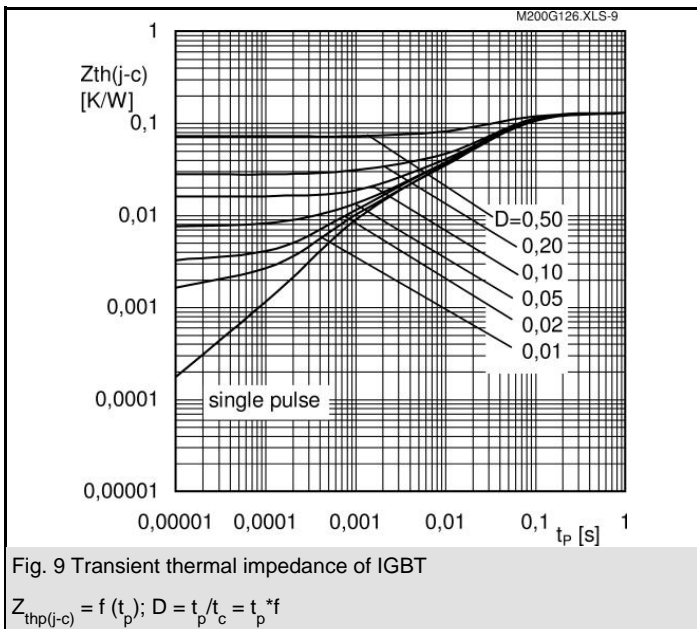
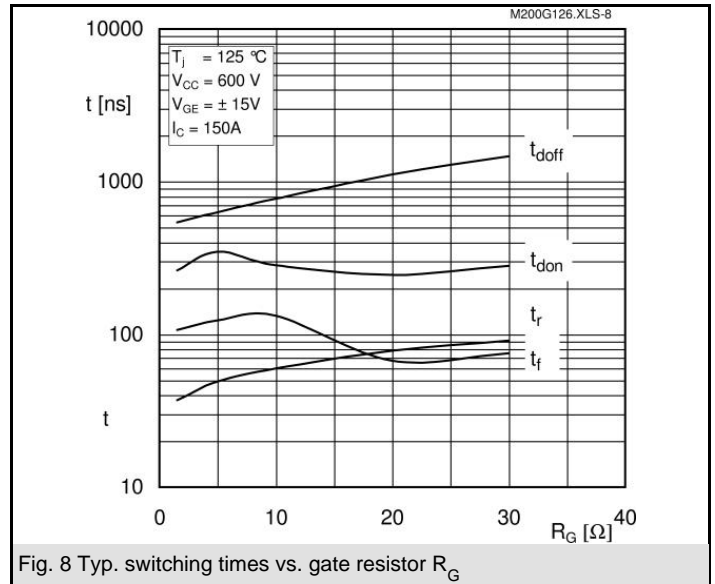
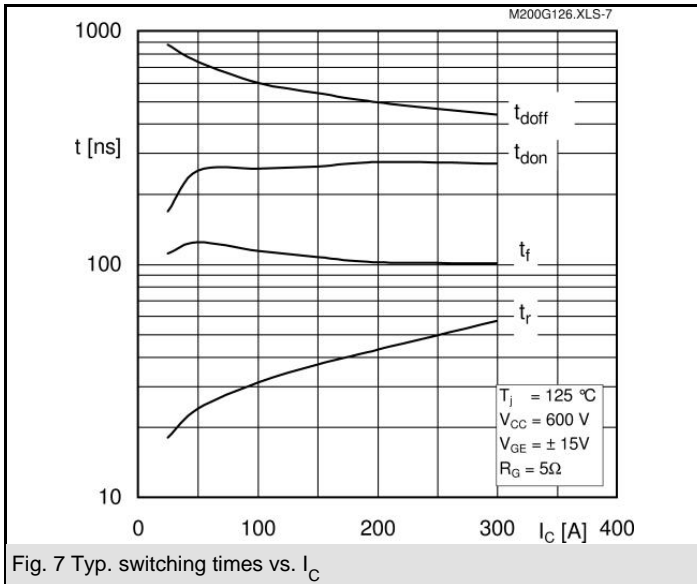
Typical Applications

- Electronic welders
- AC inverter drives
- UPS

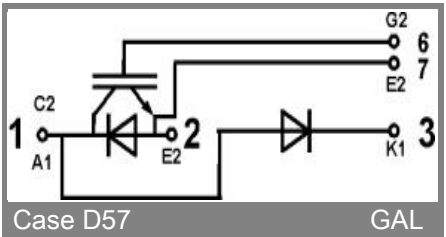
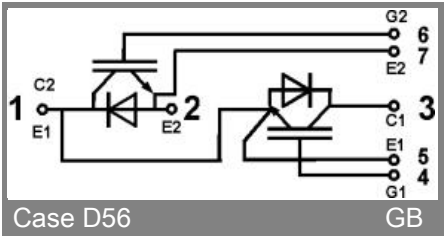
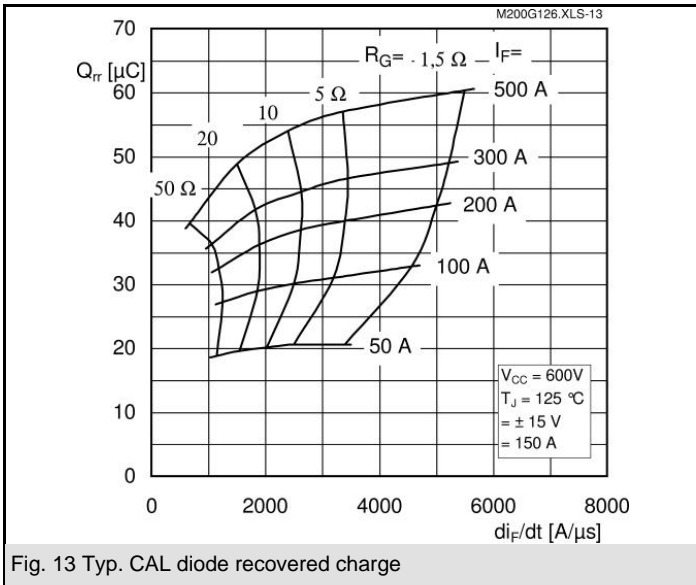


Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	Values			Units
IGBT					
V_{CES}		1200			V
I_C	$T_c = 25 (80)^\circ\text{C}$	260 (190)			A
I_{CRM}	$t_p = 1 \text{ ms}$	300			A
V_{GES}		± 20			V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)			$^\circ\text{C}$
V_{isol}	AC, 1 min.	4000			V
Inverse diode					
I_F	$T_c = 25 (80)^\circ\text{C}$	200 (140)			A
I_{FRM}	$t_p = 1 \text{ ms}$	300			A
I_{FSM}	$t_p = 10 \text{ ms; sin.}; T_j = 150^\circ\text{C}$	1100			A
Freewheeling diode					
I_F	$T_c = 25 (80)^\circ\text{C}$	200 (140)			A
I_{FRM}	$t_p = 1 \text{ ms}$	300			A
I_{FSM}	$t_p = 10 \text{ ms; sin.}; T_j = 150^\circ\text{C}$	1100			A
Characteristics		$T_{case} = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 6 \text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0, V_{CE} = V_{CES}, T_j = 25 (125)^\circ\text{C}$		0,1	0,3	mA
$V_{CE(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,9)	1,2 (1,1)	V
r_{CE}	$V_{GE} = 15 \text{ V}, T_j = 25 (125)^\circ\text{C}$		4,7 (7,3)	6,3 (9)	m Ω
$V_{CE(sat)}$	$I_{Cnom} = 150 \text{ A}, V_{GE} = 15 \text{ V}$, chip level		1,7 (2)	2,15 (2,45)	V
C_{ies}	under following conditions		10,8		nF
C_{oes}	$V_{GE} = 0, V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}$		0,9		nF
C_{res}			0,9		nF
L_{CE}				20	nH
$R_{CC'+EE'}$	res., terminal-chip $T_c = 25 (125)^\circ\text{C}$		0,35 (0,5)		m Ω
$t_{d(on)}$	$V_{CC} = 600 \text{ V}, I_{Cnom} = 150 \text{ A}$		260		ns
t_r	$R_{Gon} = R_{Goff} = 1,5 \Omega, T_j = 125^\circ\text{C}$		40		ns
$t_{d(off)}$	$V_{GE} \pm 15 \text{ V}$		540		ns
t_f			110		ns
$E_{on} (E_{off})$			18 (24)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 150 \text{ A}; V_{GE} = 0 \text{ V}; T_j = 25 (125)^\circ\text{C}$		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,8)	1,1 (0,9)	V
r_T	$T_j = 25 (125)^\circ\text{C}$		4 (5,3)	4,7 (6)	m Ω
I_{RRM}	$I_{Fnom} = 150 \text{ A}; T_j = 25 (125)^\circ\text{C}$		240		A
Q_{rr}	$di/dt = 5000 \text{ A}/\mu\text{s}$		42		μC
E_{rr}	$V_{GE} = 0 \text{ V}$		18		mJ
FWD					
$V_F = V_{EC}$	$I_F = 150 \text{ A}; V_{GE} = 0 \text{ V}, T_j = 25 (125)^\circ\text{C}$		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,8)	1,1 (0,9)	V
r_T	$T_j = 25 (125)^\circ\text{C}$		4 (5,3)	4,7 (6)	m Ω
I_{RRM}	$I_F = 150 \text{ A}; T_j = 125 ()^\circ\text{C}$		240		A
Q_{rr}	$di/dt = 5000 \text{ A}/\mu\text{s}$		42		μC
E_{rr}	$V_{GE} = 0 \text{ V}$		18		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,13	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,3	K/W
$R_{th(j-c)FD}$	per FWD			0,3	K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M5	2,5		5	Nm
w				325	g





SKM 200GB126D ...



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.